

March 19, 2004

To: Commissioner for Patents P.O.Box 1450

Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572 28 Davis Avenue

Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/758,317 01/15/04

Vincent S. Chang et al.

HIGH TEMPERATURE HYDROGEN ANNEALING OF A GATE INSULATOR LAYER TO INCREASE ETCHING SELECTIVITY BETWEEN CONDUCTIVE GATE STRUCTURE AND GATE INSULATOR LAYER

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on March 25, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

TSMC-03-287/51

- U.S. Patent 6,335,278 to Miyazaki, "Method of Hydrogen Anneal to a Semiconductor Substrate, "discloses a method of hydrogen annealling a semiconductor substrate for forming a semiconductor device such as a semiconductor integrated circuit in order to improve device performance and reliability.
- U.S. Patent 6,569,741 to Houston et al., "Hydrogen Anneal before Gate Oxidation, " discloses a process for preparing a silicon surface for gate dielectric formation.

Sincerely,

Stephen B. Ackerman,

Reg. No. 37761

Form PTO-1	449)							······································	Docker (Ameter (Openus) Application Human				
MEVE	117	۱۲۱	\cap	LI I	חופ	20	41.7	761105 0	U∩ITATI!	TSMC-03-287/51 10/758,317				
ONDE	100 Y	11. NI.	OI A	N	AF	op op		CATION	HOITATI	TSMC-03-287/51 10/758,317 Applicant Vincent S. Changetal. [Hng Data Ol/15/04 Grapp AT UM]				
1 0	والماس	ر ق	V0/.	al si	λου	ts il	Ina	לאניזוס		thing Down OI 15/04 Group LIT UM				
MAR 2 9 20	04	5							II S' PATE	INT DOCUMENTS				
MAR 2 9 70	00	DOCUMENT HUMBER					R	DATE	0.0.17	CLLII	Macmit	VAN	DATE	
	6	6335278				7	જ	1/1/02	minazati		438	110	LI D 12/2/44	
					-1 1	Migazaki Houston et al.			660 12/7/99		/ 77			
	6	3	6	9	7	4	L	5/27/03	Housto	n et al.	438	290	9/2	llor
				_		_				·				
·.														** ** **
							_							
										,				
			\dashv											
			-	-		-								
	\vdash		-								-	-		
						_	-							
	J				لــا	نـــا		ļ	I FORFIGN PA	TENT DOCUMENTS	<u> </u>		J	
						_	- 					Transla	tica	
	000	ะบม	En	T NL	Jun	en	. !	ו יוועם	ca	אַדאנ	CLASS	1 SUBCLASS		
	<u></u>	ะบม	ėπ	ר אנ	Jub	EN		CUTE	cα	YЛТИL	CUSS	SUBCLASS	YES	МО
		- เบม	ėir —	ר אנ	Jub	ien		OUTE	ca	YATKI	CUSS	SUBCLASS		
		CUM	en	ר אנ	Jub	EN		CATE	ca	YATAY	CUSS	SUBCLASS		
		CUL	en	THU	Jub	En		CATE	ca	HTRY	CUSS	SUBCLASS		
		CUL	CIC.	THU	JUB	IEN		CATE	ca	JATRY	CUSS	SUBCLASS		
		CUM	en en	ר אנ		ien		CATE	ca	JATRY	CUSS	SUBCLASS		
		COM	en en	THE		ien			OTHER DOC			Dala, Partiners	YES	
		CUM	ės c	THU		ien							YES	
		CUM	en	THU									YES	
			en	THU		ien -							YES	
			en	THU	Jub	ien							YES	
		CUM	ėn en	THU									YES	
			ėw ————————————————————————————————————	THU									YES	
EXJUMEN			EN TO THE TOTAL PROPERTY OF THE TOTAL PROPER	THU	Jug	ien							YES	
				THU	Jug					UMENTS (Including Lu			YES	